EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2067	anodiz$3 same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:20
L2	20	anodiz$3 with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:31
L3	242	porous with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:32
L4	8	porous with semiconductor same seal$3 same anodiz$4	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:22
L5	11	("4692994" | "5371037" | "5374564" | "5773355" | "5856229" | "5863830" | "5869387" | "6171982" | "6238990" | "6407367" | "6413874").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/04/16 14:29
L6	244	438/935.ccls.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/04/16 14:30
L7	111	438/913.ccls.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/04/16 14:30
L8	277	438/540.ccls.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/04/16 14:30
L9	921	438/459.ccls.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/04/16 14:30
L10	301	438/715.ccls.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/04/16 14:30
L11	264	438/311.ccls.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/04/16 14:30
L12	774	438/660.ccls.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/04/16 14:30
L13	1702	438/149.ccls.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/04/16 14:30
L14	383	438/308.ccls.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/04/16 14:30

L15	380	438/406.ccls.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/04/16 14:30
L16	1176	438/455.ccls.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/04/16 14:30
L17	921	438/459.ccls.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/04/16 14:30
L18	562	438/478.ccls.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/04/16 14:30
L19	807	438/479.ccls.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/04/16 14:31
L20	116	438/480.ccls.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/04/16 14:31
L21	338	438/481.ccls.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/04/16 14:31
L22	0	6 and anodiz$3 with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:31
L23	0	7 and anodiz$3 with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:31
L24	0	8 and anodiz$3 with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:31
L25	0	9 and anodiz$3 with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:31
L26	0	10 and anodiz$3 with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:31
L27	0	11 and anodiz$3 with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:31
L28	0	12 and anodiz$3 with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:31
L29	0	13 and anodiz$3 with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:31

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L30	0	14 and anodiz$3 with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:31
L31	1	15 and anodiz$3 with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:31
L32	0	16 and anodiz$3 with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:32
L33	0	17 and anodiz$3 with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:32
L34	0	18 and anodiz$3 with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:32
L35	0	19 and anodiz$3 with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:32
L36	0	20 and anodiz$3 with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:32
L37	0	21 and anodiz$3 with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:32
L38	0	22 and porous with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:32
L39	0	23 and porous with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:32
L40	0	24 and porous with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:32
L41	0	25 and porous with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:32
L42	0	26 and porous with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:32
L43	0	27 and porous with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:32
L44	1	6 and porous with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:33

L45	1	7 and porous with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:33
L46	1	8 and porous with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:33
L47	4	9 and porous with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:33
L48	1	10 and porous with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:33
L49	2	11 and porous with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:33
L50	2	12 and porous with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:33
L51	4	13 and porous with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:33
L52	2	14 and porous with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:33
L53	1	15 and porous with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:33
L54	4	16 and porous with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:35
L55	4	17 and porous with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:33
L56	1	18 and porous with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:33
L57	3	19 and porous with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:33
L58	1	20 and porous with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:33
L59	1	21 and porous with semiconductor same seal$3	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:33

L60	3	54 and (epi or epitaxial)	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:44
L61	0	60 and omplant$4	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:44
L62	3	60 and (implant$4 or dop$4)	USPAT; JPO; DERWENT	OR	ON	2006/04/16 14:45